

Supporting Information for

Terahertz photodetectors arrays based on large scale MoSe₂ monolayer

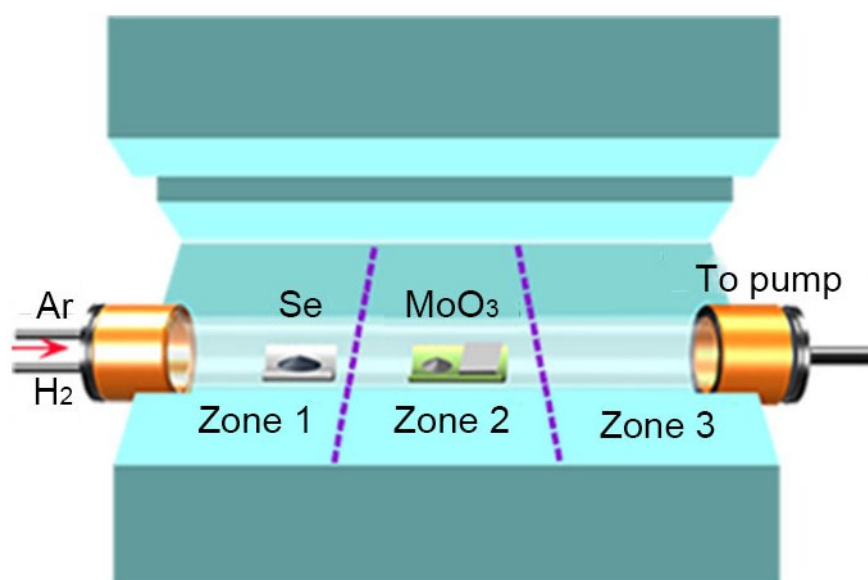
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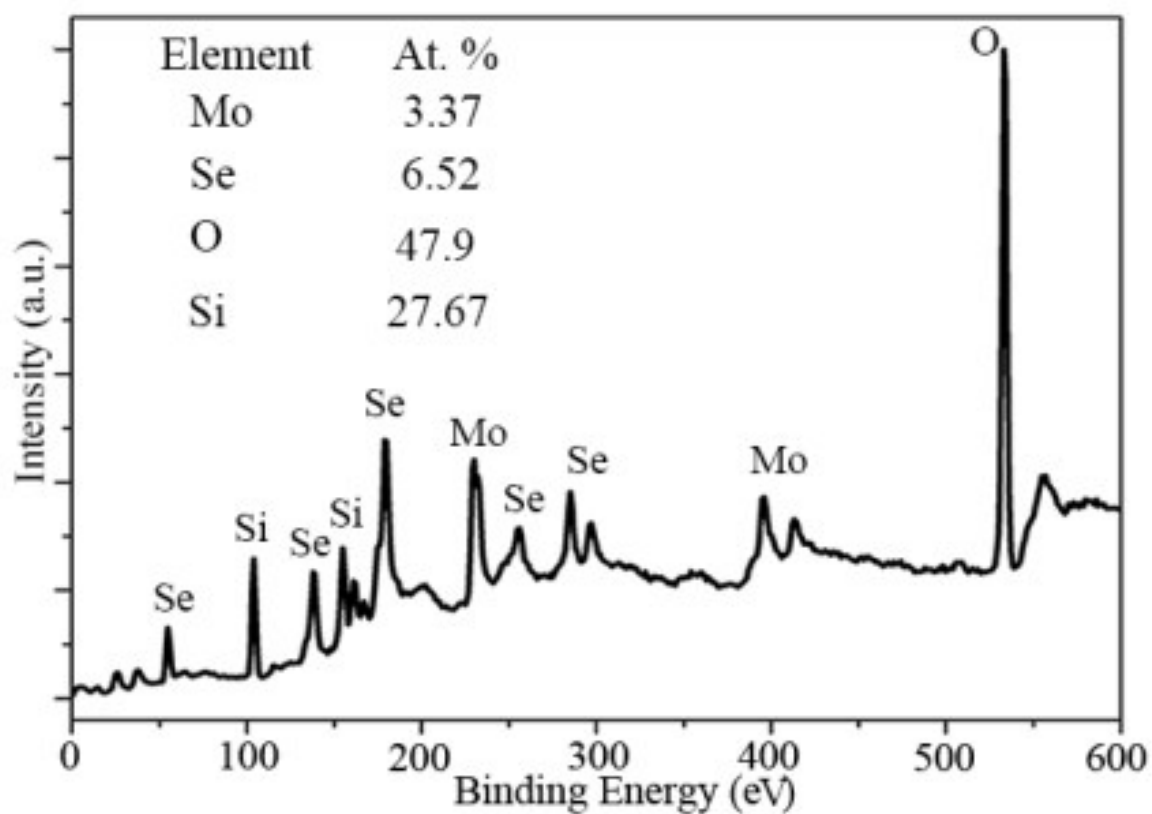
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Supplementary Figure 1. A schematic illustration of the MoSe₂ CVD system. It should be noted that the SiO₂/Si substrate with the polished side faced downward.



Supplementary Figure 2. XPS spectrum of the sample. Four elements are present: Mo and Se (from the sample), Si and O (from the substrate).